



FMMT494Q

120V NPN SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT23

Feature

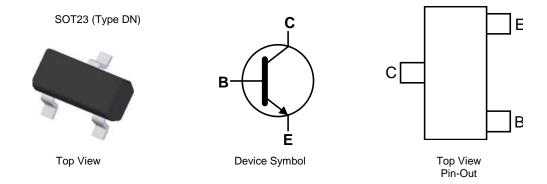
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Feature

- BV_{CEO} > 120V
- I_C = 1A Continuous Collector Current
- I_{CM} = 2A Peak Pulse Current
- 500mW Power Dissipation
- h_{FE} characterised up to 1A for high current gain hold up
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: SOT23 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @\$
- Weight: 0.008 grams (Approximate)



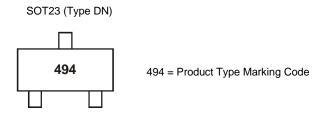
Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FMMT494QTA	Automotive	494	7	8	3,000
FMMT494QTC	Automotive	494	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	140	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	Ісм	2	Α
Base Current	I _B	200	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	500	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	250	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{ heta JL}$	197	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

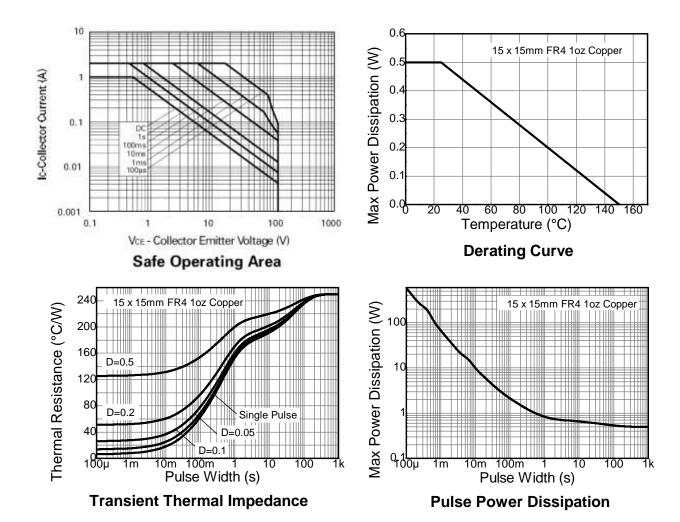
^{6.} For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	140	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	120	_	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	$I_{E} = 100 \mu A$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	V _{CB} = 120V
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 5V
Collector Emitter Cutoff Current	I _{CES}	_	_	100	nA	V _{CE} = 120V
	h _{FE}	100	_	_	_	$I_C = 1mA$, $V_{CE} = 10V$
Static Forward Current Transfer Ratio (Note 9)		100	_	300		$I_C = 250 \text{mA}, V_{CE} = 10 \text{V}$
Static Forward Current Transfer Ratio (Note 9)		60	_	_		$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
		20	_	_		$I_C = 1A$, $V_{CE} = 10V$
Collector Emitter Seturation Voltage (Note 0)	V _{CE(sat)}	_	_	200	mV	$I_C = 250 \text{mA}, I_B = 25 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	_	300		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage(Note 9)	V _{BE(on)}	_	_	1.0	V	$I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$
Base-Emitter Saturation Voltage(Note 9)	$V_{BE(sat)}$	_	_	1.1	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Output Capacitance	C _{obo}	_	_	10	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f⊤	100		_	MHz	V _{CE} = 50V, I _C = 10mA, f = 100MHz

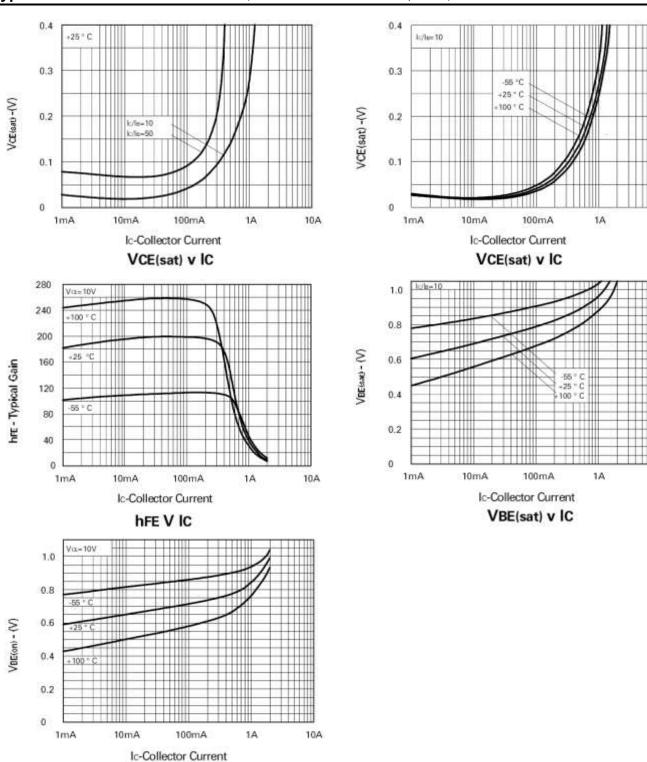
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

10A

10A



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



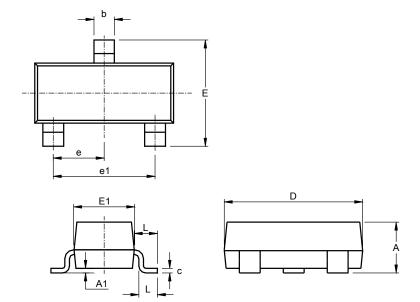
VBE(on) v IC



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 Type DN

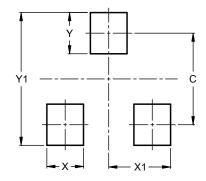


	SOT23 Type DN				
Dim	Min	Max	Тур		
Α	0.89	1.12	1.00		
A1	0.01	0.10	0.05		
b	0.30	0.51	0.45		
С	0.08	0.20	0.10		
D	2.80	3.04	3.00		
Е	2.10	2.64	2.42		
E1	1.20	1.40	1.37		
е	0.95 REF				
e1	1.90 REF				
L	0.25	0.60	0.30		
L1	0.45	0.62	0.54		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 Type DN



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
V1	2.0		



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